

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

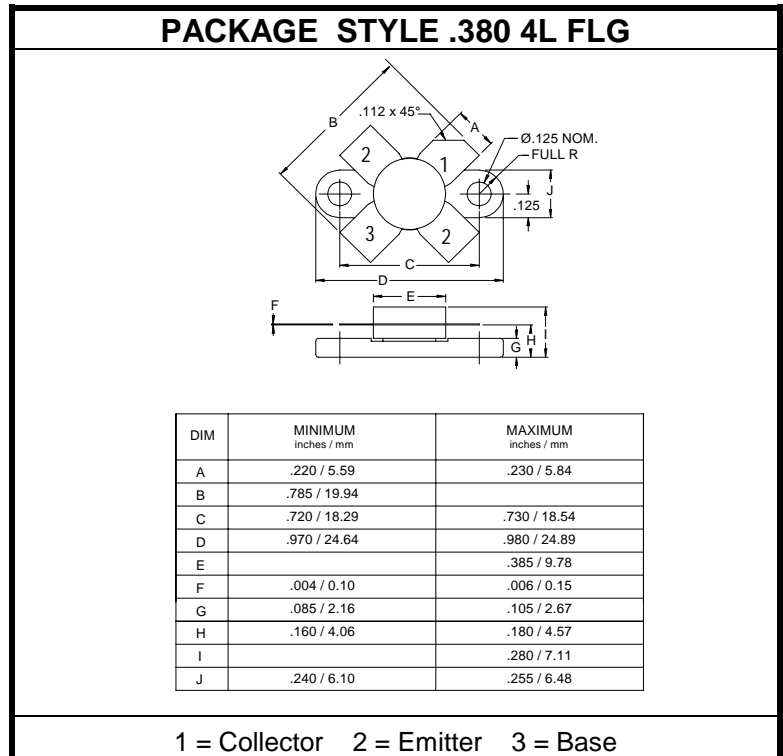
The **ASI CD2315** is designed for broadband amplifier applications in commercial and amateur communication equipment.

**FEATURES:**

- $P_G = 18$  dB min. at 75 W/30 MHz
- $IMD_3 = -30$  dBc max. at 75 W (PEP)
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	10 A
$V_{CB}$	60 V
$V_{CE}$	35 V
$P_{DISS}$	140 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.05 °C/W


**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA			35			V
$BV_{CER}$	$I_C = 50$ mA	$R_{BE} = 10$ Ω		60			V
$BV_{EBO}$	$I_E = 10$ mA			4.0			V
$I_{CES}$	$V_E = 28$ V					5	mA
$h_{FE}$	$V_{CE} = 5.0$ V	$I_C = 1.0$ A		10		100	---
$C_{ob}$	$V_{CB} = 28$ V	f = 1.0 MHz				80	pF
$G_{PE}$	$V_{CE} = 25$ V	$I_{CQ} = 3.2$ A	f = 225 MHz	13.5	14.5		dB
$IMD_3$	$P_{REF} = 16$ W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB			-55	dBc

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.